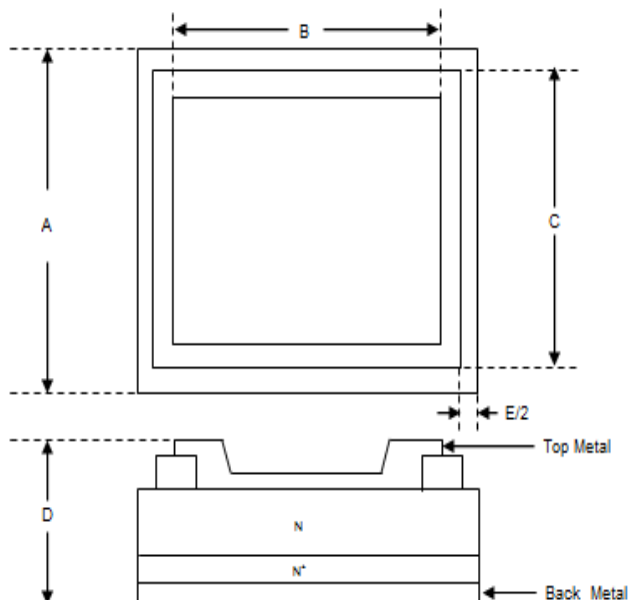


Trench Schottky Barrier Diode Wafer (TSBD)

Preliminary


Item	Dimensions	
	um	mil
Die Size (A)	380	15
Top Metal Pad Size (B)	330	13
Passivation Seal (C)	340	13.4
Wafer Thickness (D)	150	6
Scribe Line Width (E)	40	1.57
Other Informations		
Wafer Size	6"	
Gross Die	109100	
Top Metal	Al	
Back Metal	Ag	

Electrical Characteristics @TA=25 °C				
Item	Symbol	Spec. Limit	Die Sort	Unit
Maximum Repetitive Peak Reverse Voltage @0.2mA	V_{RRM}	45	46	V
Maximum Average Forward Rectified Current	I_o	1		A
Forward Voltage Drop, @ $I_F=0.5A$ @ $I_F=1A$	V_F	0.47 0.55	0.45	V
Maximum Reverse Current at Rated V_{RRM}	I_R	40	20	μA
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	5		A
Operating Temperature Range	T_J	-50 to +125		°C
Storage Temperature Range	T_{STG}	-50 to +150		°C